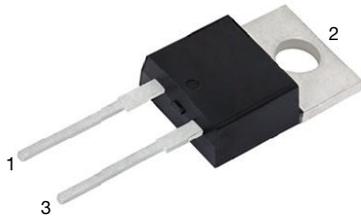
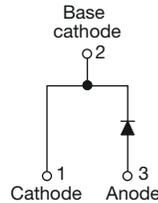


# HEXFRED<sup>®</sup>, Ultrafast Soft Recovery Diode, 6 A


**2L TO-220AC**


## FEATURES

- Ultrafast and ultrasoft recovery
- Very low  $I_{RRM}$  and  $Q_{rr}$
- Designed and qualified according to JEDEC<sup>®</sup>-JESD 47
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
 COMPLIANT  
 HALOGEN  
**FREE**

## BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

## DESCRIPTION

VS-HFA06TB120 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 6 A continuous current, the VS-HFA06TB120 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED<sup>®</sup> product line features extremely low values of peak recovery current ( $I_{RRM}$ ) and does not exhibit any tendency to “snap-off” during the  $t_b$  portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA06TB120 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

### PRIMARY CHARACTERISTICS

$I_{F(AV)}$	6 A
$V_R$	1200 V
$V_F$ at $I_F$	3.0 V
$t_{rr}$ typ.	26 ns
$T_J$ max.	150 °C
Package	2L TO-220AC
Circuit configuration	Single

### ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Cathode to anode voltage	$V_R$		1200	V
Maximum continuous forward current	$I_F$	$T_C = 100\text{ °C}$	6	A
Single pulse forward current	$I_{FSM}$		80	
Maximum repetitive forward current	$I_{FRM}$		24	
Maximum power dissipation	$P_D$	$T_C = 25\text{ °C}$	62.5	W
		$T_C = 100\text{ °C}$	25	
Operating junction and storage temperature range	$T_J, T_{Stg}$		-55 to +150	°C



<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	$V_{BR}$	$I_R = 100\text{ }\mu\text{A}$	1200	-	-	V
Maximum forward voltage	$V_{FM}$	$I_F = 6.0\text{ A}$	-	2.7	3.0	
		$I_F = 12\text{ A}$	-	3.5	3.9	
		$I_F = 6.0\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	2.4	2.8	
Maximum reverse leakage current	$I_{RM}$	$V_R = V_R$ rated	-	0.26	5.0	$\mu\text{A}$
		$T_J = 125\text{ }^\circ\text{C}, V_R = 0.8 \times V_R$ rated	-	110	500	
Junction capacitance	$C_T$	$V_R = 200\text{ V}$	-	9.0	14	pF
Series inductance	$L_S$	Measured lead to lead 5 mm from package body	-	8.0	-	nH

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Reverse recovery time	$t_{rr}$	$I_F = 1.0\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}, V_R = 30\text{ V}$	-	26	-	ns
	$t_{rr1}$	$T_J = 25\text{ }^\circ\text{C}$	-	53	80	
	$t_{rr2}$	$T_J = 125\text{ }^\circ\text{C}$	-	87	130	
Peak recovery current	$I_{RRM1}$	$T_J = 25\text{ }^\circ\text{C}$	-	4.4	8.0	A
	$I_{RRM2}$	$T_J = 125\text{ }^\circ\text{C}$	-	5.0	9.0	
Reverse recovery charge	$Q_{rr1}$	$T_J = 25\text{ }^\circ\text{C}$	-	116	320	nC
	$Q_{rr2}$	$T_J = 125\text{ }^\circ\text{C}$	-	233	585	
Peak rate of recovery current during $t_b$	$di_{(rec)M}/dt1$	$T_J = 25\text{ }^\circ\text{C}$	-	180	-	$\text{A}/\mu\text{s}$
	$di_{(rec)M}/dt2$	$T_J = 125\text{ }^\circ\text{C}$	-	100	-	

<b>THERMAL - MECHANICAL SPECIFICATIONS</b>						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	$T_{lead}$	0.063" from case (1.6 mm) for 10 s	-	-	300	$^\circ\text{C}$
Thermal resistance, junction to case	$R_{thJC}$		-	-	2.0	K/W
Thermal resistance, junction to ambient	$R_{thJA}$	Typical socket mount	-	-	80	
Thermal resistance, case to heatsink	$R_{thCS}$	Mounting surface, flat, smooth, and greased	-	0.5	-	
Weight			-	2.0	-	g
			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style 2L TO-220AC	HFA06TB120			

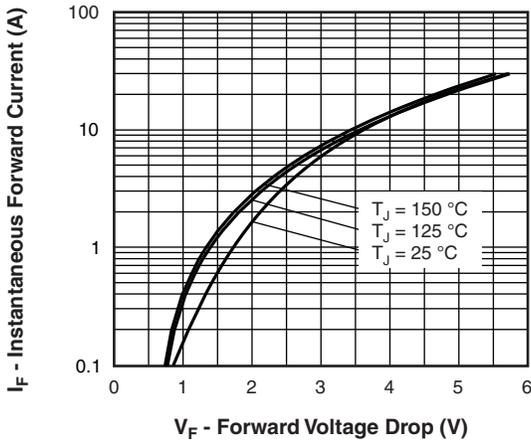


Fig. 1 - Typical Forward Voltage Drop Characteristics

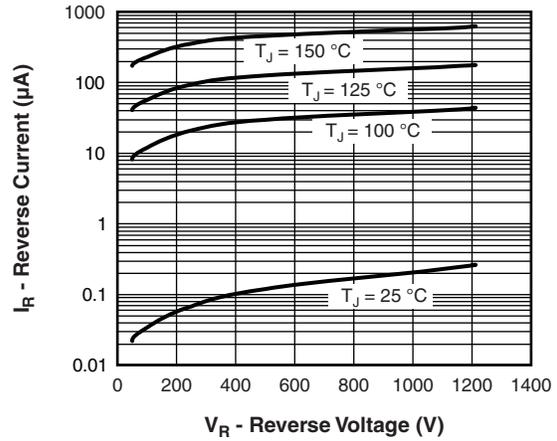


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

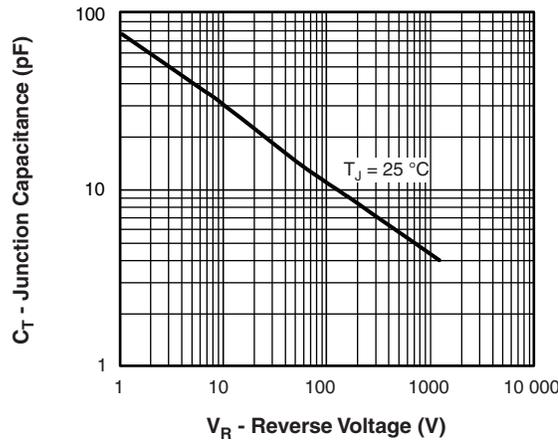


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

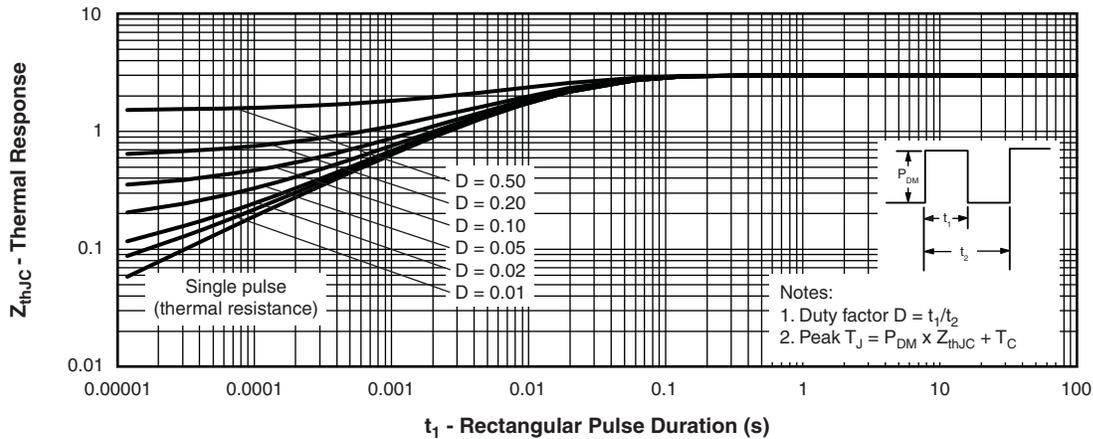


Fig. 4 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics

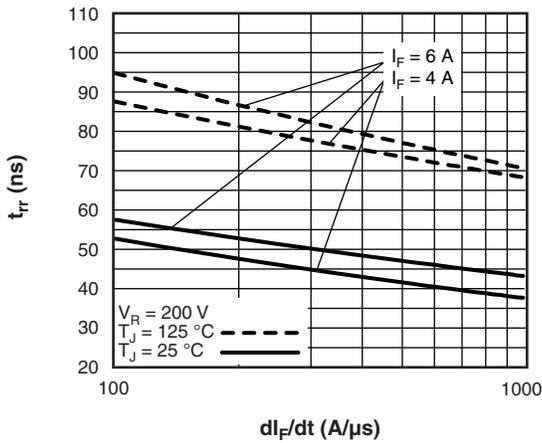


Fig. 5 - Typical Reverse Recovery Time vs.  $di_F/dt$

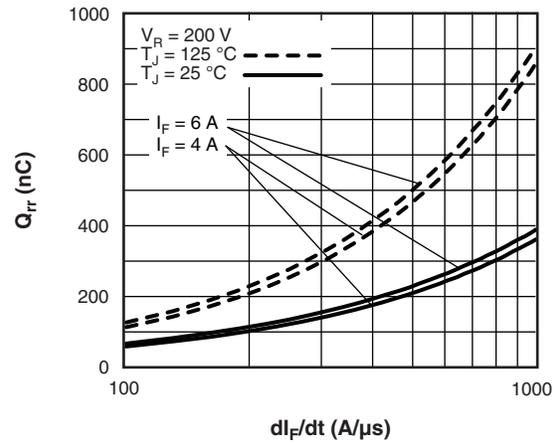


Fig. 7 - Typical Stored Charge vs.  $di_F/dt$

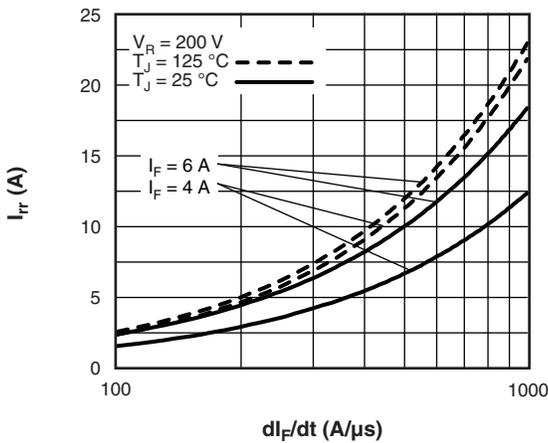


Fig. 6 - Typical Recovery Current vs.  $di_F/dt$

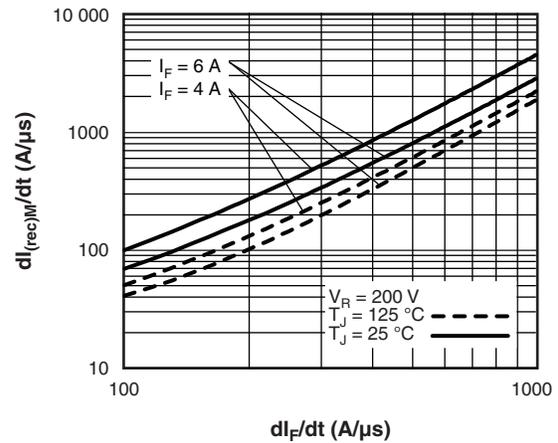
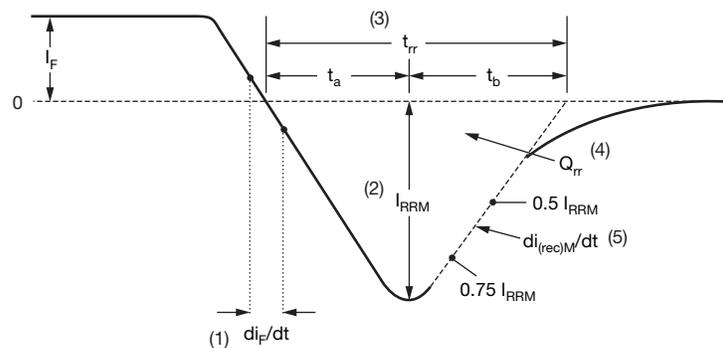


Fig. 8 - Typical  $di_{(rec)M}/dt$  vs.  $di_F/dt$



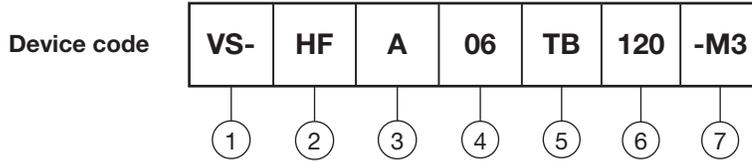
- (1)  $di_F/dt$  - rate of change of current through zero crossing
- (2)  $I_{RRM}$  - peak reverse recovery current
- (3)  $t_{rr}$  - reverse recovery time measured from zero crossing point of negative going  $I_F$  to point where a line passing through  $0.75 I_{RRM}$  and  $0.50 I_{RRM}$  extrapolated to zero current.
- (4)  $Q_{rr}$  - area under curve defined by  $t_{rr}$  and  $I_{RRM}$
- (5)  $di_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

Fig. 9 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE



- 1** - Vishay Semiconductors product
- 2** - HEXFRED® family
- 3** - Electron irradiated
- 4** - Current rating (06 = 6 A)
- 5** - Package:  
TB = 2L TO-220AC
- 6** - Voltage rating (120 = 1200 V)
- 7** - Environmental digit:  
-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

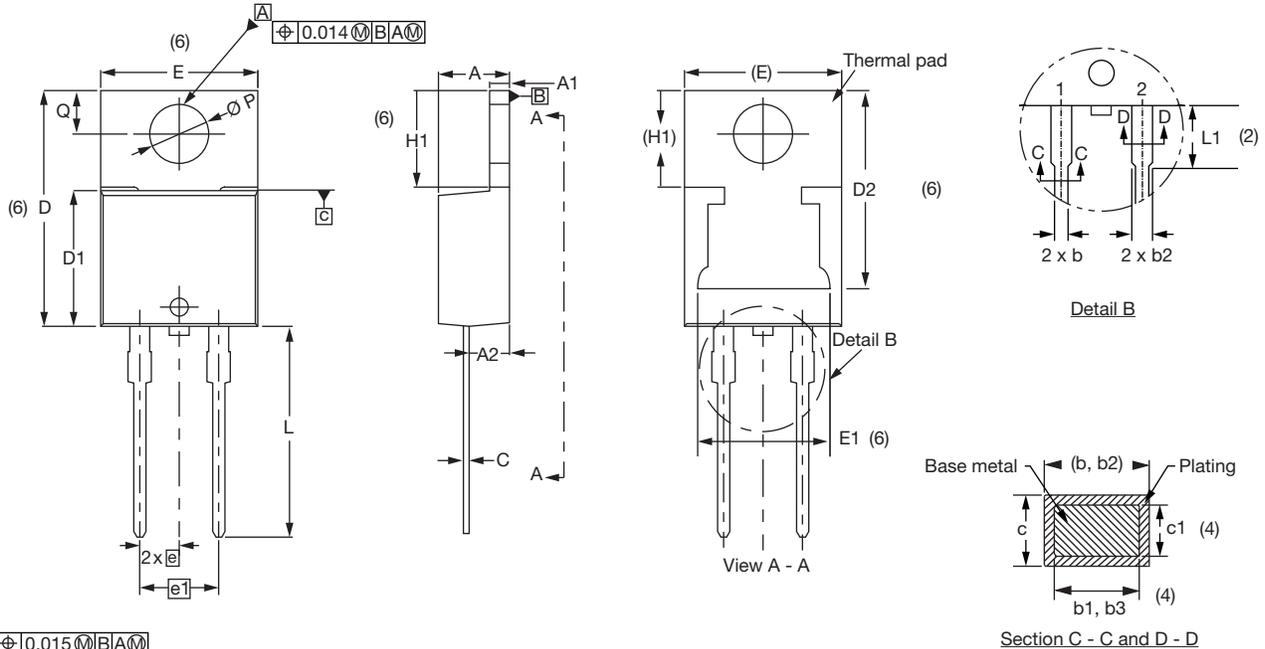
ORDERING INFORMATION (Example)			
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-HFA06TB120-M3	50	1000	Antistatic plastic tube

LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?96156">www.vishay.com/doc?96156</a>
Part marking information	<a href="http://www.vishay.com/doc?95391">www.vishay.com/doc?95391</a>



# 2L TO-220AC

**DIMENSIONS** in millimeters and inches



Conforms to JEDEC® outline TO-220AC

SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.			MIN.	MAX.	MIN.	MAX.	
A	4.25	4.65	0.167	0.183		D2	11.68	13.30	0.460	0.524	6, 7
A1	1.14	1.40	0.045	0.055		E	10.11	10.51	0.398	0.414	3, 6
A2	2.50	2.92	0.098	0.115		E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040		e	2.41	2.67	0.095	0.105	
b1	0.38	0.97	0.015	0.038	4	e1	4.88	5.28	0.192	0.208	
b2	1.20	1.73	0.047	0.068		H1	6.09	6.48	0.240	0.255	6
b3	1.14	1.73	0.045	0.068	4	L	13.52	14.02	0.532	0.552	
c	0.36	0.61	0.014	0.024		L1	3.32	3.82	0.131	0.150	2
c1	0.36	0.56	0.014	0.022	4	∅ P	3.54	3.91	0.139	0.154	
D	14.85	15.35	0.585	0.604	3	Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355							

**Notes**

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2



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